

FIS9-2000-0404US1



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re patent application of

Heemyong Park, Fariborz Assaderaghi and Jack A. Mandelman

Serial No.: not assigned

Group Art Unit: not assigned

Filed:

Examiner: Not known

For: METHOD OF BUILDING A CMOS STRUCTURE ON THIN SOI WITH
SOURCE/DRAIN ELECTRODES FORMED BY IN SITU DOPED
SELECTIVE AMORPHOUS SILICON

Commissioner of Patents and Trademarks
Washington, D.C. 20231

**INFORMATION DISCLOSURE STATEMENT
UNDER 37 C.F.R. 1.56**

Sir:

Under the provisions of 37 C.F.R. 1.97 through 1.99 and pursuant to applicant's duty of disclosure under 37 C.F.R. 1.56, applicant respectfully brings the documents listed on the attached form PTO-1449, and discussed in the Specification, to the attention of the Examiner in charge of the above-identified application. Copies of these documents are provided herewith for the convenience of the Examiner.

This citation does not constitute an admission that the references are relevant or material to the claims. They are merely cited as constituting related art of which the applicant is aware.

It is respectfully requested that these documents be considered by the Examiner and formally made of record in this application.

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Respectfully submitted,



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Karen Ling-Mars 8/8/01